

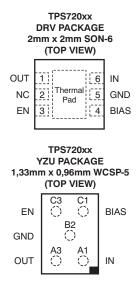
350mA, Ultra-Low V_{IN}, RF Low-Dropout Linear Regulator with Bias Pin

FEATURES

- 350mA High-Performance LDO
- Low Quiescent Current: 38µA
- Excellent Load Transient Response: ±15mV for I_{LOAD} = 0mA to 350mA in 1μs
- Excellent Line Transient Response: $\Delta V_{OUT} = \pm 2mV$ for $\Delta V_{BIAS} = \pm 600mV$ in 1µs $\Delta V_{OUT} = \pm 200\mu V$ for $\Delta V_{IN} = \pm 400mV$ in 1µs
- Low Noise: 48µV_{RMS} (10Hz to 100kHz)
- 80dB V_{IN} PSRR (10Hz to 10kHz)
- 70dB V_{BIAS} PSRR (10Hz to 10kHz)
- Fast Start-Up Time: 140μs
- Built-In Soft-Start with Monotonic V_{OUT} Rise and Startup Current Limited to 100mA + I_{LOAD}
- Over-Current and Thermal Protection
- Low Dropout: 110mV at I_{LOAD} = 350mA
- Stable with 2.2µF Output Capacitor
- Available in 1,33mm x 0,96mm WCSP-5 and 2mm x 2mm SON-6 Packages

APPLICATIONS

- Digital Cameras
- Cellular Camera Phones
- Wireless LAN
- Handheld Products



DESCRIPTION

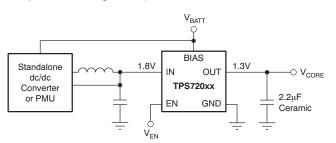
The TPS720xx family of dual rail, low-dropout linear regulators (LDOs) offers outstanding ac performance (PSRR, load and line transient response), while consuming a very low quiescent current of 38μ A.

The V_{BIAS} rail that powers the control circuit of the LDO draws very low current (on the order of the quiescent current of the LDO) and can be connected to any power supply that is equal to or greater than 1.4V above the output voltage. The main power path is through V_{IN}, which can be a lower voltage than V_{BIAS}; it can be as low as V_{OUT} + V_{DO}, increasing the efficiency of the solution in many power-sensitive applications. For example, V_{IN} can be an output of a high-efficiency, dc-dc step-down regulator.

The TPS720xx supports a novel feature in which the output of the LDO regulates under light loads when the IN pin is left floating. The light-load drive current is sourced from V_{BIAS} under this condition. This feature is particularly useful in power-saving applications where the dc/dc converter connected to the IN pin is disabled but the LDO is still required to regulate the voltage to a light load.

The TPS720xx is stable with ceramic capacitors and uses an advanced BICMOS fabrication process that yields a dropout of 110mV at a 350mA output load. The TPS720xx has the unique feature of providing a monotonic V_{OUT} rise (overshoot limited to 3%) with V_{IN} inrush current limited to 100mA + I_{LOAD} with an output capacitor of 2.2µF.

The TPS720xx uses a precision voltage reference and feedback loop to achieve overall accuracy of 2% over load, line, process, and temperature extremes. An ultra-small wafer chip-scale package (WCSP) makes the TPS720xx ideal for handheld applications. The TPS720xx is also available in a SON-8 package. This family of devices is fully specified over the temperature range of $T_{\rm u} = -40^{\circ}$ C to +125°C.



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SBVS100D-JUNE 2008-REVISED AUGUST 2009

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION⁽¹⁾

PRODUCT	V _{OUT} ⁽²⁾
	 XX is nominal output voltage (for example, 28 = 2.8V, 285 = 2.85V). YYY is the package designator. Z is tape and reel quantity (R = 3000, T = 250).

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(2) Output voltages from 0.9V to 3.6V in 50mV increments are available through the use of innovative factory EEPROM programming; minimum order quantities may apply. Contact factory for details and availability.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

At $T_J = -40^{\circ}$ C to +125°C (unless otherwise noted). All voltages are with respect to GND.

PARAMETER		TPS720xx	UNIT			
Input voltage rar	nge (steady-state), V _{IN} ⁽²⁾	-0.3 to V _{BIAS} or +5.0 ⁽³⁾	V			
Peak transient in	nput voltage, V _{IN_PEAK} ⁽⁴⁾	+5.5	V			
Bias voltage ran	ge, V _{BIAS}	-0.3 to +6.0	V			
Enable voltage r	ange, V _{EN}	-0.3 to +6.0	V			
Output voltage ra	ange, V _{OUT}	-0.3 to +5.0 V				
Peak output curr	rent, I _{OUT}	Internally limited				
Output short-circ	cuit duration	Indefinite				
Total continuous	power dissipation, P _{DISS}	See Dissipation Ratings	Table			
	Human body model (HBM)	2000	V			
ESD rating	Charged device model (CDM)	500	V			
	Machine model (MM)	100	V			
Operating junction	on temperature range, T _J	-55 to +125	°C			
Storage tempera	ature range, T _{STG}	-55 to +150				

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

(2) To ensure proper operation of the device it is necessary that V_{IN} ≤ V_{BIAS} under all conditions.

(3) Whichever is less.

(4) For durations no longer than 1ms each, for a total of no more than 1000 occurrences over the lifetime of the device.

DISSIPATION RATINGS

BOARD	PACKAGE	$R_{\theta JC}$	$R_{ heta JA}$	DERATING FACTOR ABOVE T _A = +25°C	T _A < +25°C	T _A = +70°C	T _A = +85°C
High-K ⁽¹⁾	YZU	51°C/W	248°C/W	4mW/°C	403mW	222mW	160mW
High-K ⁽¹⁾	DRV	20°C/W	65°C/W	15.4mW/°C	1580mW	845mW	615mW

(1) The JEDEC high-K (2s2p) board used to derive this data was a 3- x 3-inch, multilayer board with 1-ounce internal power and ground planes and 2-ounce copper traces on top and bottom of the board.

2

ÈXAS **NSTRUMENTS**

SBVS100D-JUNE 2008-REVISED AUGUST 2009

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ELECTRICAL CHARACTERISTICS

Over operating temperature range ($T_J = -40^{\circ}C$ to +125°C), $V_{BIAS} = (V_{OUT} + 1.4V)$ or 2.5V (whichever is greater); $V_{IN} \ge V_{OUT} + 0.5V$, $I_{OUT} = 1mA$, $V_{EN} = 1.1V$, $C_{OUT} = 2.2\mu$ F, unless otherwise noted. Typical values are at $T_J = +25^{\circ}C$.

	PARAM	IETER	TEST CON	DITIONS	MIN	TYP	MAX	UNIT
V _{IN}	Input volta	age range			1.1 ⁽¹⁾		$\substack{V_{\text{BIAS}} \text{ or} \\ 4.5^{(2)}}$	V
V _{BIAS}	Bias volta	ge range			2.5		5.5	V
	Output vol	ltage range ⁽⁴⁾			0.9		3.6	V
		Nominal	$T_J = +25^{\circ}C$	-3.0		+3.0	mV	
		Over V _{BIAS} , V _{IN} , I _{OUT} , T _J = -40° C to $+125^{\circ}$ C	$\begin{array}{l} V_{OUT} + 1.4V \leq V_{BIAS} \leq 5. \\ V_{OUT} + 0.5V \leq V_{IN} \leq 4.5V \\ 0mA \leq I_{OUT} \leq 350mA \end{array}$	-2.0		+2.0	%	
V _{OUT} ⁽³⁾	Output accuracy	Over V _{BIAS} , V _{IN} , I _{OUT} , T _J = -40°C to +125°C	$\begin{array}{ c c c } \hline \textbf{DRV package only:} \\ V_{OUT} + 1.4V \leq V_{BIAS} \leq 5. \\ V_{OUT} + 0.5V \leq V_{IN} \leq 4.5V \\ 0mA \leq I_{OUT} \leq 350mA, \\ V_{OUT} < 1.2V \end{array}$	-25		+25	mV	
	Over V _{BIAS} , V _{IN} , I _{OUT} , T _J = −10°C to +85°C		$\begin{array}{l} \textbf{YZU package only:} \\ V_{OUT} + 1.4V \leq V_{BIAS} \leq 5. \\ V_{OUT} + 0.5V \leq V_{IN} \leq 4.5V \\ 0mA \leq I_{OUT} \leq 350mA \\ 1.6V \leq V_{OUT} \leq 3.3V \end{array}$	-1.0		+1.0	%	
		V _{IN} floating	$V_{OUT} + 1.4V \le V_{BIAS} \le 5.5V, \\ 0\mu A \le I_{OUT} \le 500\mu A$		±1.0		%	
$\Delta V_{OUT} / \Delta V_{IN}$	V _{IN} line re	gulation	$V_{IN} = (V_{OUT} + 0.5V)$ to 4.	5V, I _{OUT} = 1mA		16		μV/V
$\Delta V_{OUT} / \Delta V_{BIAS}$	V_{BIAS} line	regulation	$V_{BIAS} = (V_{OUT} + 1.4V)$ or greater) to 5.5V, $I_{OUT} = 1$		16		μV/V	
	V _{IN} line tra	ansient	$\Delta V_{IN} = 400 \text{mV}, t_{RISE} = t_{F}$	_{ALL} = 1µs		±200		μV
	V _{BIAS} line	transient	$\Delta V_{BIAS} = 600 \text{mV}, \text{ t}_{RISE} =$		±0.8		mV	
$\Delta V_{OUT} / \Delta I_{OUT}$	Load regu	lation	$0mA \le I_{OUT} \le 350mA$ (no	load to full load)		-15		μV/mA
	Load trans	sient	$0mA \le I_{OUT} \le 350mA$, t_{RI}	_{SE} = t _{FALL} = 1µs		±15		mV
V _{DO_IN}	V _{IN} dropou	ut voltage ⁽⁵⁾		4V,		110	200	mV
V _{DO_BIAS}	V _{BIAS} drop	oout voltage ⁽⁶⁾	$V_{\rm IN} = V_{\rm OUT(\rm NOM)} + 0.3 \rm V,$	I _{OUT} = 350mA		1.09	1.4	V
I _{CL}	Output cu	rrent limit	$V_{OUT} = 0.9 \times V_{OUT(NOM)}$		420	525	800	mA
1	Cround ni	~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~	I _{OUT} = 100μA			38		μΑ
GND	Ground pi	n current	I _{OUT} = 0mA to 350mA			54	80	μΑ
I _{SHDN}	I _{SHDN} Shutdown current (I _{GND})	current (I _{GND})	$V_{EN} \le 0.4$ V, $T_J = -40$ °C to	o +85°C		0.5	2	μA
				f = 10Hz		85		dB
				f = 100Hz		85		dB
PSRR	V power	supply rejection ratio	$V_{IN} - V_{OUT} \ge 0.5V,$	f = 1kHz		85		dB
FORR	viN power	-supply rejection ratio	V _{BIAS} = V _{OUT} + 1.4V, I _{OUT} = 350mA	f = 10kHz		80		dB
				f = 100kHz		70		dB
				f = 1MHz		50		dB

Performance specifications are ensured up to a minimum $V_{IN} = V_{OUT} + 0.5V$. Whichever is less. (1)

- (2)
- (3)
- (4)
- (5)
- $\begin{array}{l} \text{Minimum V}_{\text{BIAS}} = (V_{\text{OUT}} + 1.4V) \text{ or } 2.5V \text{ (whichever is greater) and } V_{\text{IN}} = V_{\text{OUT}} + 0.5V. \\ V_{\text{O}} \text{ nominal value is factory programmable through the onchip EEPROM.} \\ \text{Measured for devices with } V_{\text{OUT}(\text{NOM})} \geq 1.2V. \\ V_{\text{BIAS}} V_{\text{OUT}} \text{ with } V_{\text{OUT}} = V_{\text{OUT}(\text{NOM})} 0.1V. \\ \text{Measured for devices with } V_{\text{OUT}(\text{NOM})} \geq 1.8V. \end{array}$ (6)

SBVS100D-JUNE 2008-REVISED AUGUST 2009

ELECTRICAL CHARACTERISTICS (continued)

Over operating temperature range ($T_J = -40^{\circ}C$ to +125°C), $V_{BIAS} = (V_{OUT} + 1.4V)$ or 2.5V (whichever is greater); $V_{IN} \ge V_{OUT} + 0.5V$, $I_{OUT} = 1mA$, $V_{EN} = 1.1V$, $C_{OUT} = 2.2\mu$ F, unless otherwise noted. Typical values are at $T_J = +25^{\circ}C$.

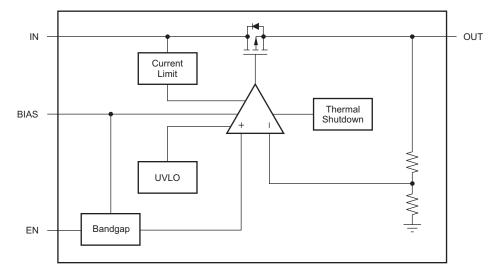
	PARAMETER	TEST CON	DITIONS	MIN	TYP	MAX	UNIT
					80		dB
			f = 100Hz		80		dB
PSRR	V nower eventy rejection ratio	$V_{IN} - V_{OUT} \ge 0.5V,$	f = 1kHz		75		dB
PORK	V _{BIAS} power-supply rejection ratio	$V_{BIAS} = V_{OUT} + 1.4V,$ $I_{OUT} = 350mA$	f = 10kHz		65		dB
			f = 100kHz		55		dB
			f = 1MHz		35		dB
V _N	Output noise voltage	BW = 10Hz to 100kHz, $V_{IN} = V_{OUT} + 0.5V$	V _{BIAS} ≥ 2.5V,		48		μV_{RMS}
I _{VIN_INRUSH}	Inrush current on V _{IN}	$V_{BIAS} = (V_{OUT} + 1.4V)$ or greater), $V_{IN} = V_{OUT} + 0$			100 + I _{LOAD}		mA
t _{STR}	Startup time	$\label{eq:Vout} \begin{array}{l} V_{OUT} = 95\% \ V_{OUT(NOM)}, \\ C_{OUT} = 2.2 \mu F \end{array}$	I _{OUT} = 350mA,		140		μs
V _{EN(HI)}	Enable pin high (enabled)			1.1			V
V _{EN(LO)}	Enable pin low (disabled)			0		0.4	V
I _{EN}	Enable pin current	$V_{EN} = 5.5V, V_{IN} = 4.5V,$	V _{BIAS} = 5.5V			1.0	μA
	Undervoltage lockout	V _{BIAS} rising		2.41	2.45	2.49	V
UVLO	Hysteresis	V _{BIAS} falling			150		mV
-		Shutdown, temperature	increasing		+160		°C
T _{SD}	Thermal shutdown temperature	Reset, temperature dec		+140		°C	
TJ	Operating junction temperature			-40		+125	°C

4



SBVS100D-JUNE 2008-REVISED AUGUST 2009

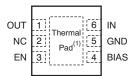
DEVICE INFORMATION

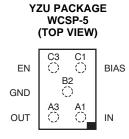


Functional Block Diagram

PIN CONFIGURATION

DRV PACKAGE SON-6 (TOP VIEW)





 It is recommended that the SON (DRV) package thermal pad be connected to ground.

PIN DESCRIPTIONS

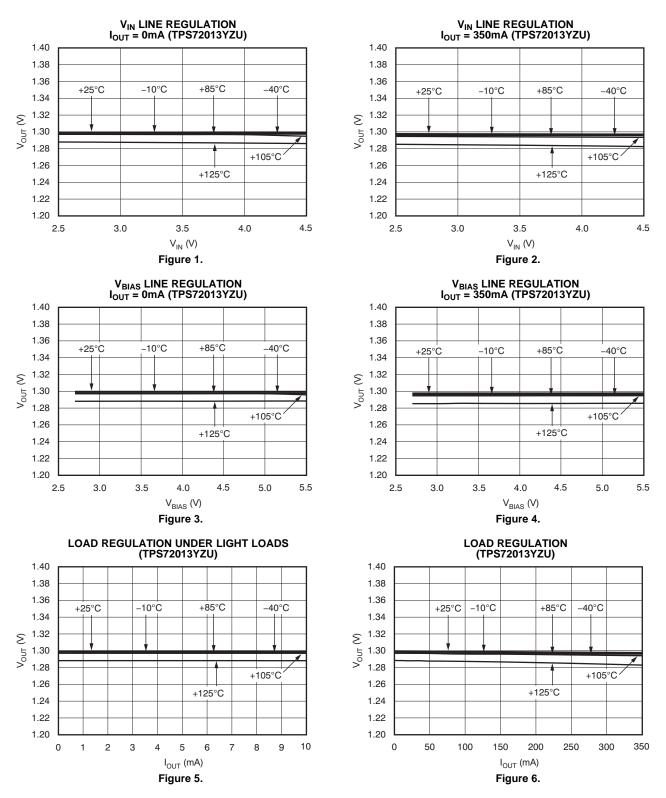
TP	S720xx		
NAME	DRV	YZU	DESCRIPTION
OUT	1	A3	Output pin. A 2.2µF ceramic capacitor is connected from this pin to ground, for stability and to provide load transients. See <i>Input and Output Capacitor Requirements</i> in the <i>Application Information</i> section.
NC	2		No connection.
EN	3	C3	Enable pin. A logic high signal on this pin turns the device on and regulates the voltage from IN to OUT. A logic low on this pin turns off the device.
BIAS	4	C1	Bias supply pin. It is recommended that this input be bypassed with a ceramic capacitor to ground for better transient performance. See <i>Input and Output Capacitor Requirements</i> in the <i>Application Information</i> section.
GND	5	B2	Ground pin.
IN	6	A1	Input pin. This pin can be a maximum of 4.5V; V _{IN} must not exceed V _{BIAS} . Bypass this input with a ceramic capacitor to ground. See <i>Input and Output Capacitor Requirements</i> in the <i>Application Information</i> section.

5

SBVS100D-JUNE 2008-REVISED AUGUST 2009

TYPICAL CHARACTERISTICS

Over operating temperature range ($T_J = -40^{\circ}C$ to +125°C), $V_{BIAS} = (V_{OUT} + 1.4V)$ or 2.5V (whichever is greater); $V_{IN} = V_{OUT} + 0.5V$, $I_{OUT} = 1$ mA, $V_{EN} = 1.1V$, $C_{OUT} = 2.2\mu$ F, unless otherwise noted. Typical values are at $T_J = +25^{\circ}C$.





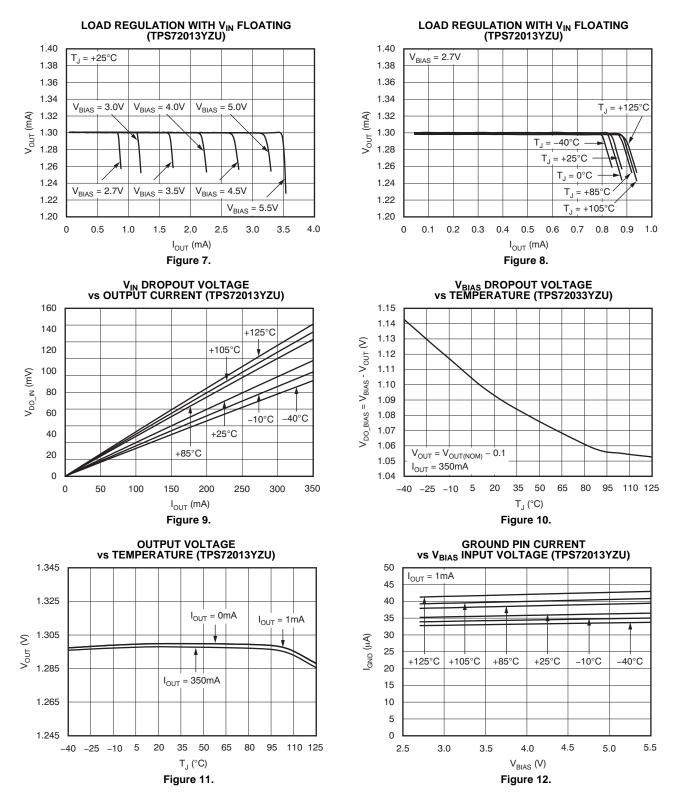
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TYPICAL CHARACTERISTICS (continued)

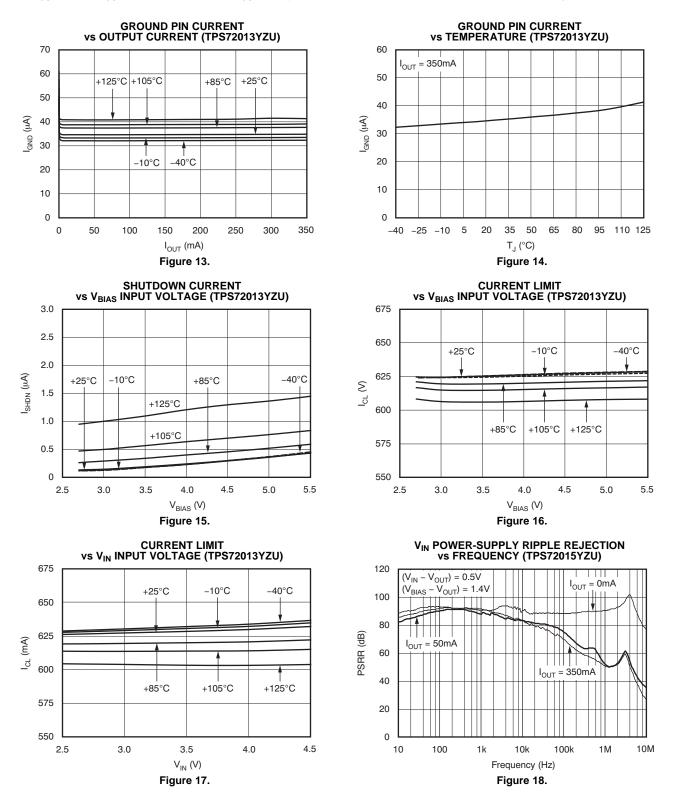
Over operating temperature range ($T_J = -40^{\circ}C$ to +125°C), $V_{BIAS} = (V_{OUT} + 1.4V)$ or 2.5V (whichever is greater); $V_{IN} = V_{OUT} + 0.5V$, $I_{OUT} = 1$ mA, $V_{EN} = 1.1V$, $C_{OUT} = 2.2\mu$ F, unless otherwise noted. Typical values are at $T_J = +25^{\circ}C$.



SBVS100D-JUNE 2008-REVISED AUGUST 2009

TYPICAL CHARACTERISTICS (continued)

Over operating temperature range (T_J = -40°C to +125°C), V_{BIAS} = (V_{OUT} + 1.4V) or 2.5V (whichever is greater); $V_{IN} = V_{OUT} + 0.5V$, $I_{OUT} = 1$ mA, $V_{EN} = 1.1V$, $C_{OUT} = 2.2\mu$ F, unless otherwise noted. Typical values are at $T_J = +25^{\circ}$ C.



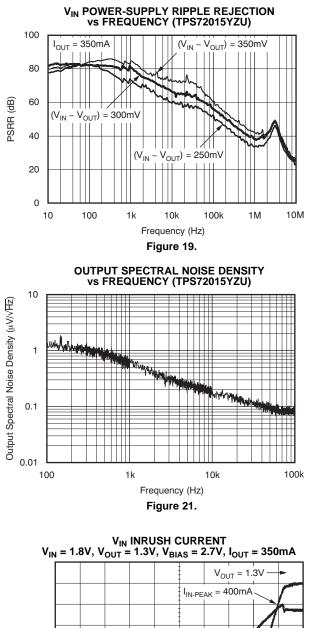
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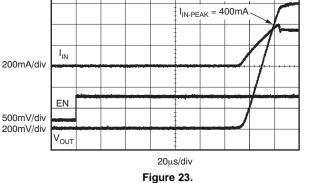


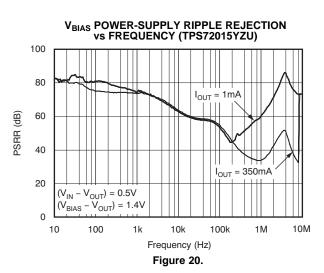
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TYPICAL CHARACTERISTICS (continued)

Over operating temperature range ($T_J = -40^{\circ}C$ to +125°C), $V_{BIAS} = (V_{OUT} + 1.4V)$ or 2.5V (whichever is greater); $V_{IN} = V_{OUT} + 0.5V$, $I_{OUT} = 1$ mA, $V_{EN} = 1.1V$, $C_{OUT} = 2.2\mu$ F, unless otherwise noted. Typical values are at $T_J = +25^{\circ}C$.







 $\label{eq:VIN} \begin{array}{l} V_{IN} \mbox{ INRUSH CURRENT} \\ V_{IN} = 1.8V, \ V_{OUT} = 1.3V, \ V_{BIAS} = 2.7V, \ I_{OUT} = 0 mA \end{array}$

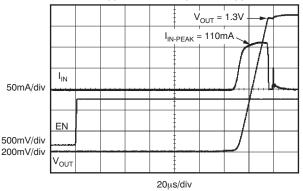
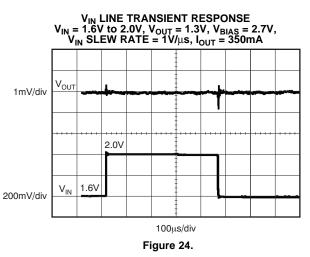


Figure 22.



9

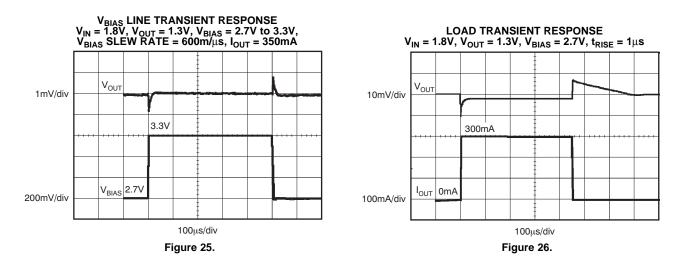
TEXAS INSTRUMENTS

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TYPICAL CHARACTERISTICS (continued)

Over operating temperature range ($T_J = -40^{\circ}C$ to +125°C), $V_{BIAS} = (V_{OUT} + 1.4V)$ or 2.5V (whichever is greater); $V_{IN} = V_{OUT} + 0.5V$, $I_{OUT} = 1$ mA, $V_{EN} = 1.1V$, $C_{OUT} = 2.2\mu$ F, unless otherwise noted. Typical values are at $T_J = +25^{\circ}C$.



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APPLICATION INFORMATION

The TPS720xx belongs to a family of new generation LDO regulators that use innovative circuitry to achieve ultra-wide bandwidth and high loop gain, resulting in extremely high PSRR (up to 1MHz) at very low headroom ($V_{IN} - V_{OUT}$). The implementation of the BIAS pin on the TPS720xx vastly improves efficiency of low $V_{\mbox{\scriptsize OUT}}$ applications by allowing the use of a preregulated, low-voltage input supply. The TPS720xx supports a novel feature in which the output of the LDO regulates under light loads (<500µA) when the IN pin is left floating. The light-load drive current is sourced from V_{BIAS} under this condition. This feature is particularly useful in power-saving applications where the dc/dc converter connected to the IN pin is disabled but the LDO is still required to regulate the voltage to a light load. These features, combined with low noise, low ground pin current, and ultra-small packaging, make this device ideal for portable applications. This family of regulators offers sub-bandgap output voltages, current limit and thermal protection, and is fully specified from -40°C to +125°C.

INPUT AND OUTPUT CAPACITOR REQUIREMENTS

Although an input capacitor is not required for stability on the IN pin, it is good analog design practice to connect a 0.1μ F to 1.0μ F low equivalent series resistance (ESR) capacitor across the IN pin input supply near the regulator. This capacitor counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated, or if the device is located close to the power source. If source impedance is not sufficiently low, a 0.1μ F input capacitor may be necessary to ensure stability.

The BIAS pin does not require an input capacitor because it does not source high currents. However, if source impedance is not sufficiently low, a small 0.1μ F bypass capacitor is recommended.

The TPS720xx is designed to be stable with standard ceramic capacitors with values of 2.2μ F or larger at the output. X5R- and X7R-type capacitors are best because they have minimal variation in value and ESR over temperature. Maximum ESR should be less than 250m Ω .

BOARD LAYOUT RECOMMENDATIONS TO IMPROVE PSRR AND NOISE PERFORMANCE

To improve ac performance such as PSRR, output noise, and transient response, it is recommended that the board be designed with separate ground planes for $V_{\rm IN}$ and $V_{\rm OUT}$, with the ground plane connected only at the GND pin of the device. In addition, the

ground connection for the output capacitor should be connected directly to the GND pin of the device. High equivalent series resistance (ESR) capacitors may degrade PSRR. The BIAS pin draws very little current and can be routed as a signal (make sure to shield it from high-frequency coupling).

INTERNAL CURRENT LIMIT

The TPS720xx internal current limits help protect the regulator during fault conditions. During current limit, the output sources a fixed amount of current that is largely independent of output voltage. In such a case, the output voltage is not regulated, and is $V_{OUT} = I_{LIMIT} \times R_{LOAD}$. The NMOS pass transistor dissipates ($V_{IN} - V_{OUT}$) × I_{LIMIT} until thermal shut down is triggered and the device is turned off. As the device cools down, it is turned on by the internal thermal shutdown circuit. If the fault condition continues, the device cycles between current limit and thermal shutdown. See the *Thermal Information* section for more details.

The NMOS pass element in the TPS720xx has a built-in body diode that conducts current when the voltage at OUT exceeds the voltage at IN. This current is not limited, so if extended reverse voltage operation is anticipated, external limiting to 5% of rated output current is recommended.

INRUSH CURRENT LIMIT

The TPS720xx family of LDO regulators implement a novel inrush current-limit circuit architecture: the current drawn through the IN pin is limited to a finite value. This $I_{INRUSHLIMIT}$ charges the output to its final voltage. All the current drawn through V_{IN} goes to charge the output capacitance when the load is disconnected. The following equation shows the inrush current limit performed by the circuit:

$$I_{\text{INRUSHLIMIT}}(A) = C_{\text{OUT}}(\mu F) \times 0.0454545(V/\mu s) + I_{\text{IOAD}}(A)$$
(1)

Assuming a C_{OUT} of 2.2µF with the load disconnected (that is, $I_{LOAD} = 0$) the $I_{INRUSHLIMIT}$ is calculated to be 100mA. The inrush current charges the LDO output capacitor. If the output of the LDO regulates to 1.3V, then the LDO charges the output capacitor to the final output value in approximately 28.6µs.

Another consideration is when a load is connected to the output of an LDO. The connected load tries to steer a portion of the current away from V_{OUT}. The TPS720xx inrush current-limit circuit employs a new technique that supplies not only the I_{INRUSHLIMIT}, but also the additional current needed by the load. If I_{LOAD} = 350mA, then the I_{INRUSHLIMIT} calculates to be approximately 450mA (from Equation 1).

SBVS100D-JUNE 2008-REVISED AUGUST 2009

SHUTDOWN

The enable pin (EN) is active high and is compatible with standard and low voltage, TTL-CMOS levels. When shutdown capability is not required, EN can be connected to the IN pin.

DROPOUT VOLTAGE

The TPS720xx uses a NMOS pass transistor to achieve low dropout. When $(V_{\rm IN}-V_{OUT})$ is less than the dropout voltage $(V_{\rm DO})$, the NMOS pass device is in the linear region of operation and the input-to-output resistance is the $R_{\rm DS(ON)}$ of the NMOS pass element. $V_{\rm DO}$ approximately scales with output current because the NMOS device behaves as a resistor in dropout.

As with any linear regulator, PSRR and transient response are degraded as $(V_{IN} - V_{OUT})$ approaches dropout. This effect is shown in Figure 19 in the *Typical Characteristics* section.

TRANSIENT RESPONSE

As with any regulator, increasing the size of the output capacitor reduces over/undershoot magnitude but increases duration of the transient response.

UNDERVOLTAGE LOCK-OUT (UVLO)

The TPS720xx uses an undervoltage lock-out circuit on the BIAS pin to keep the output shut off until the internal circuitry is operating properly. The UVLO circuit has a deglitch feature so that it typically ignores undershoot transients on the input if they are less than 50μ s duration.

MINIMUM LOAD

The TPS720xx is stable with no output load. Traditional LDOs suffer from low loop gain at very light output loads. The TPS720xx employs an innovative, low-current mode circuit under very light or no-load conditions, resulting in improved output voltage regulation performance down to zero output current.

OUTPUT REGULATION WITH IN PIN FLOATING

The TPS720xx supports a novel feature in which the output of the LDO regulates under light loads when the IN pin is left floating. Under normal conditions, when the IN pin is connected to a power source, the BIAS pin draws only tens of milliamperes. However, when the IN pin is floating, an innovative circuit is used that allows a mximum current of 500μ A to be drawn by the load through the BIAS pin, while maintaining the output in regulation. This feature is particularly useful in power-saving applications where a dc/dc converter connected to the IN pin is disabled, but the LDO is required to regulate the output voltage to a light load.

Figure 27 shows an application example where a microcontroller is not turned off (to maintain the state of the internal memory), but where the regulated supply (shown as the TPS62xxx) is turned off to reduce power. In this case, the TPS720xx BIAS pin provides sufficient load current to maintain a regulated voltage to the microcontroller.

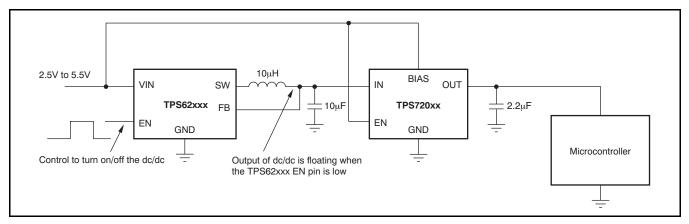


Figure 27. Example of Floating IN Pin Regulation



THERMAL INFORMATION

Thermal protection disables the output when the junction temperature rises to approximately +160°C, allowing the device to cool. When the junction temperature cools to approximately +140°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the dissipation of the regulator, protecting it from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heatsink. For reliable operation, junction temperature should be limited to +125°C maximum. To estimate the margin of safety in a complete design heatsink), increase (including the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions. For good reliability, thermal protection should trigger at least +35°C above the maximum expected ambient particular application. condition of the This configuration produces a worst-case junction temperature of +125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the TPS720xx has been designed to protect against overload conditions. It was not intended to replace proper heatsinking. Continuously running the TPS720xx into thermal shutdown degrades device reliability.

POWER DISSIPATION

The ability to remove heat from the die is different for each package type, presenting different considerations in the printed circuit board (PCB) layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Performance data for JEDEC lowand high-K boards are given in the *Dissipation Ratings* table. Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers also improves the heatsink effectiveness.

SBVS100D-JUNE 2008-REVISED AUGUST 2009

Power dissipation depends on input voltage and load conditions. Power dissipation (P_D) is equal to the product of the output current times the voltage drop across the output pass element (V_{IN} to V_{OUT}), as shown in Equation 2:

$$P_{\rm D} = (V_{\rm IN} - V_{\rm OUT}) \times I_{\rm OUT}$$
(2)

PACKAGE MOUNTING

Solder pad footprint recommendations for the TPS720xx are available from the Texas Instruments web site at www.ti.com.

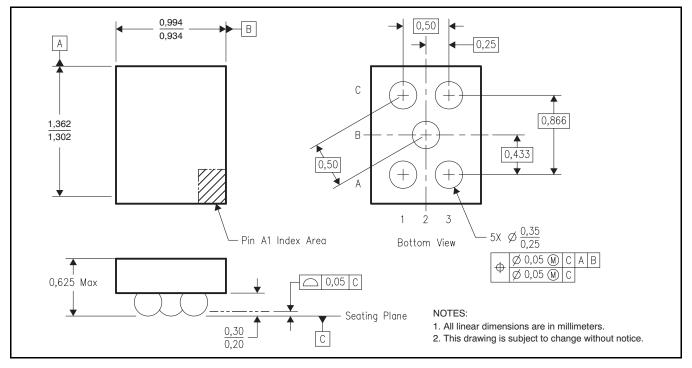


Figure 28. YZU Wafer Chip-Scale Package Dimensions (in mm)



REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision C (September, 2008) to Revision D	Pag	е
•	Added electrical specifications for DRV package		3
•	Noted electrical specifications for YZU package		3



24-Jan-2013

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
TPS72009YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	G3	Samples
TPS72009YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	G3	Samples
TPS720105DRVR	ACTIVE	SON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	ODC	Samples
TPS720105DRVT	ACTIVE	SON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	ODC	Samples
TPS720105YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	NM	Samples
TPS720105YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	NM	Samples
TPS72010DRVR	ACTIVE	SON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAA	Samples
TPS72010DRVT	ACTIVE	SON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAA	Samples
TPS720115DRVR	ACTIVE	SON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	SHP	Samples
TPS720115DRVT	ACTIVE	SON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	SHP	Samples
TPS72011DRVR	ACTIVE	SON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	PAR	Samples
TPS72011DRVT	ACTIVE	SON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	PAR	Samples
TPS72011YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	BQ	Samples
TPS72011YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	BQ	Samples
TPS72012DRVR	ACTIVE	SON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAB	Samples
TPS72012DRVT	ACTIVE	SON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAB	Samples
TPS72012YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	NN	Samples



PACKAGE OPTION ADDENDUM

24-Jan-2013

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
TPS72012YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125		Samples
TPS72013YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	FS	Samples
TPS72013YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	FS	Samples
TPS72015DRVR	ACTIVE	SON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAC	Samples
TPS72015DRVT	ACTIVE	SON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAC	Samples
TPS72015YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	FT	Samples
TPS72015YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	FT	Samples
TPS72017YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	GC	Samples
TPS72017YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	GC	Samples
TPS72018DRVR	ACTIVE	SON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAD	Samples
TPS72018DRVT	ACTIVE	SON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DAD	Samples
TPS72018YZUR	ACTIVE	DSBGA	YZU	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	GD	Samples
TPS72018YZUT	ACTIVE	DSBGA	YZU	5	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	GD	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.



24-Jan-2013

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.

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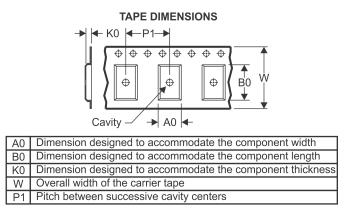
PACKAGE MATERIALS INFORMATION

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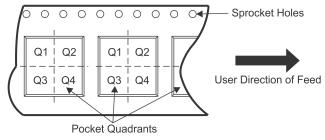
Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS72009YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72009YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS720105DRVR	SON	DRV	6	3000	330.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS720105DRVT	SON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS720105DRVT	SON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS720105YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS720105YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72010DRVR	SON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72010DRVT	SON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS720115DRVR	SON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS720115DRVT	SON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72011DRVR	SON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72011DRVT	SON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72011YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72011YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72012DRVR	SON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72012DRVT	SON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72012YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1

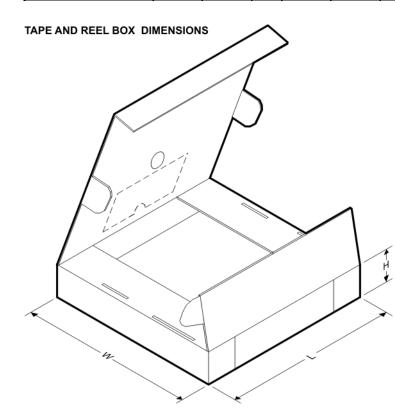
PACKAGE MATERIALS INFORMATION



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21-Mar-2013

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS72012YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72013YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72013YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72015DRVR	SON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72015DRVT	SON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72015YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72015YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72017YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72017YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72018DRVR	SON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72018DRVT	SON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS72018YZUR	DSBGA	YZU	5	3000	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1
TPS72018YZUT	DSBGA	YZU	5	250	180.0	8.4	1.07	1.42	0.74	4.0	8.0	Q1



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS72009YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS72009YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0
TPS720105DRVR	SON	DRV	6	3000	367.0	367.0	35.0
TPS720105DRVT	SON	DRV	6	250	203.0	203.0	35.0

PACKAGE MATERIALS INFORMATION



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						[1
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS720105DRVT	SON	DRV	6	250	210.0	185.0	35.0
TPS720105YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS720105YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0
TPS72010DRVR	SON	DRV	6	3000	203.0	203.0	35.0
TPS72010DRVT	SON	DRV	6	250	203.0	203.0	35.0
TPS720115DRVR	SON	DRV	6	3000	203.0	203.0	35.0
TPS720115DRVT	SON	DRV	6	250	203.0	203.0	35.0
TPS72011DRVR	SON	DRV	6	3000	203.0	203.0	35.0
TPS72011DRVT	SON	DRV	6	250	203.0	203.0	35.0
TPS72011YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS72011YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0
TPS72012DRVR	SON	DRV	6	3000	203.0	203.0	35.0
TPS72012DRVT	SON	DRV	6	250	203.0	203.0	35.0
TPS72012YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS72012YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0
TPS72013YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS72013YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0
TPS72015DRVR	SON	DRV	6	3000	203.0	203.0	35.0
TPS72015DRVT	SON	DRV	6	250	203.0	203.0	35.0
TPS72015YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS72015YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0
TPS72017YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS72017YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0
TPS72018DRVR	SON	DRV	6	3000	203.0	203.0	35.0
TPS72018DRVT	SON	DRV	6	250	203.0	203.0	35.0
TPS72018YZUR	DSBGA	YZU	5	3000	210.0	185.0	35.0
TPS72018YZUT	DSBGA	YZU	5	250	210.0	185.0	35.0

MECHANICAL DATA

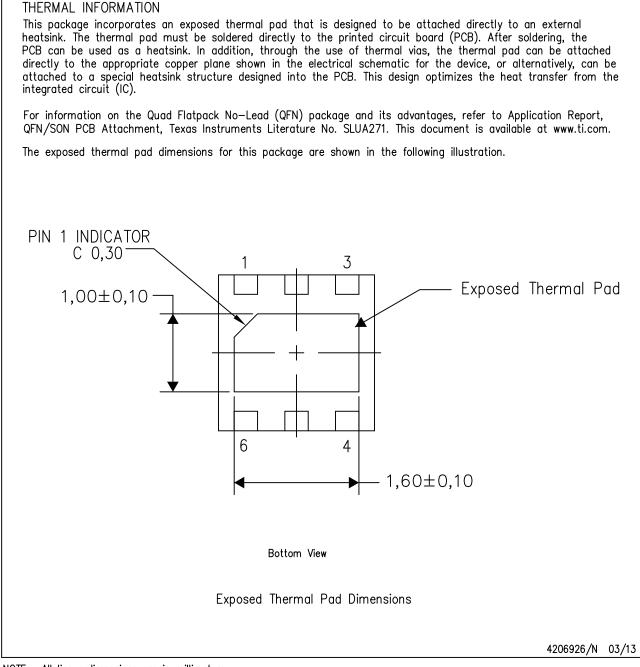


- C. Small Outline No-Lead (SON) package configuration.
- The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.



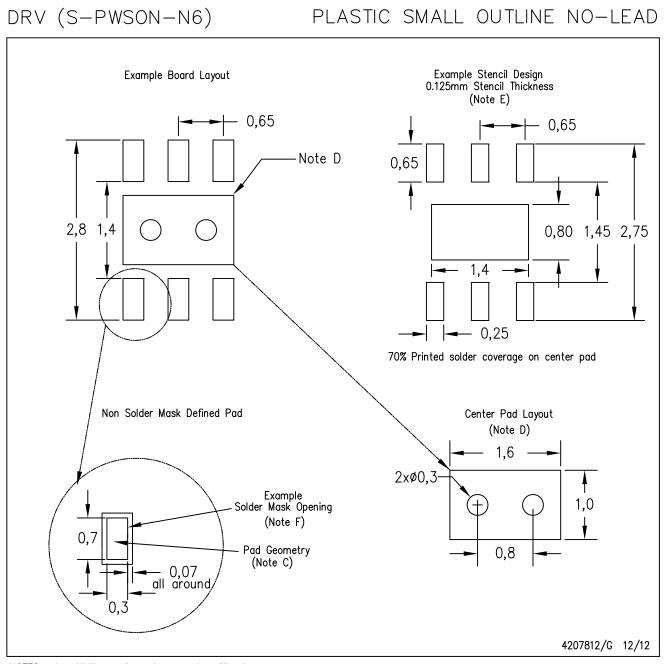
DRV (S-PWSON-N6)

PLASTIC SMALL OUTLINE NO-LEAD



NOTE: All linear dimensions are in millimeters





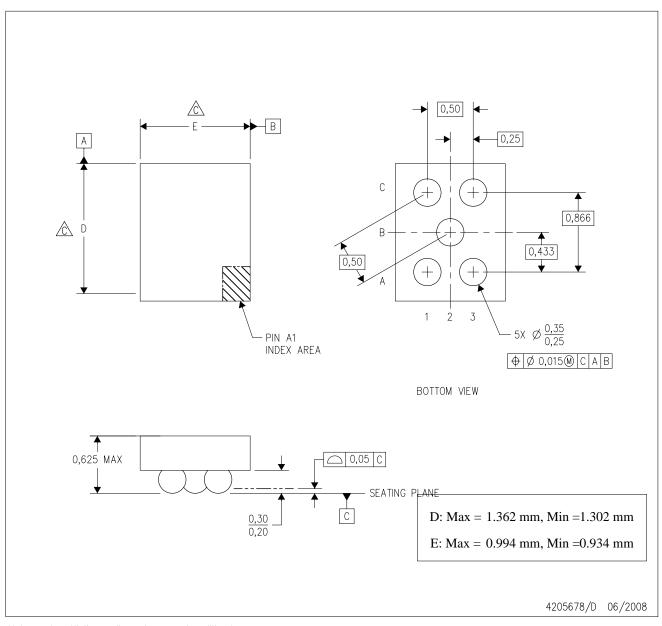
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for solder mask tolerances.



YZU (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



- Notes: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - Devices in this YZQ package can have dimension D ranging from 1.31 to 1.75 mm and dimension E ranging from 0.94 to 1.45 mm. To determine the exact package size of a particular device, refer to the device datasheet or contact a local TI representative.
 D. NanoFree™ package configuration.
 - E. This package contains lead-free balls. Refer to the 5 YEU package (drawing 4205430) for tin-lead (SnPb) balls.

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